

MMBTA06WT1

Driver Transistor

NPN Silicon

Moisture Sensitivity Level: 1
ESD Rating: Human Body Model – 4 kV
Machine Model – 400 V

Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	80	Vdc
Collector–Base Voltage	V_{CBO}	80	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	500	mAdc

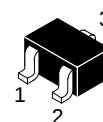
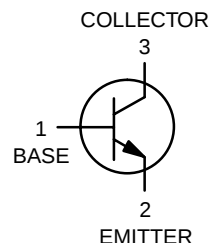
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$



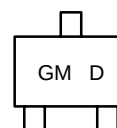
ON Semiconductor®

<http://onsemi.com>



SC-70
CASE 419
STYLE 3

MARKING DIAGRAM



GM = Specific Device Code
D = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA06WT1	SC-70	3000/Tape & Reel
MMBTA06WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	80	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CES}	–	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.1	μAdc

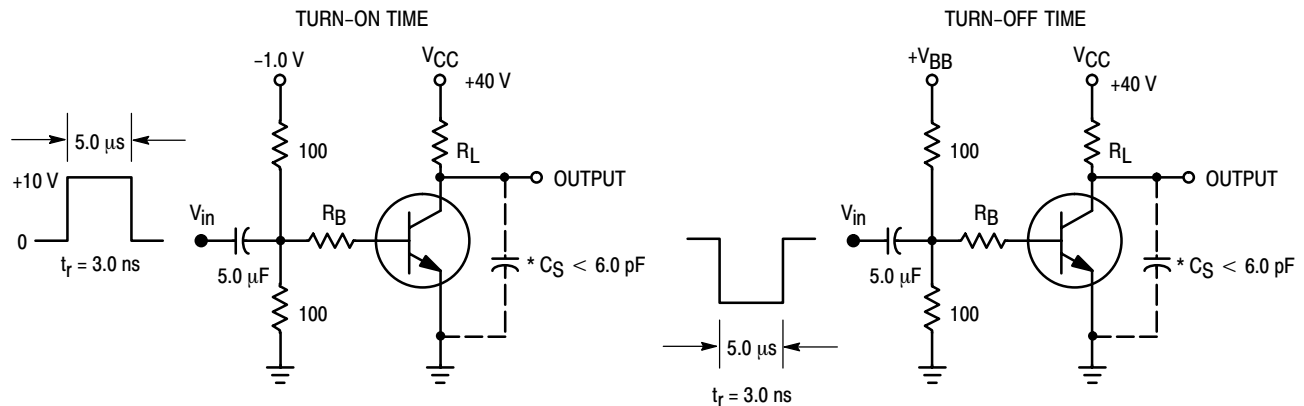
ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	100 100	– –	–
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	–	0.25	Vdc
Base–Emitter On Voltage ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 2) ($I_C = 10\text{ mA}$, $V_{CE} = 2.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	–	MHz
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1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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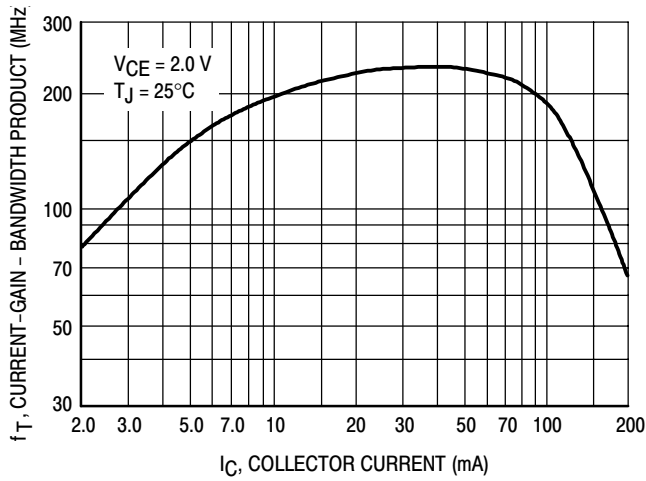


Figure 2. Current-Gain — Bandwidth Product

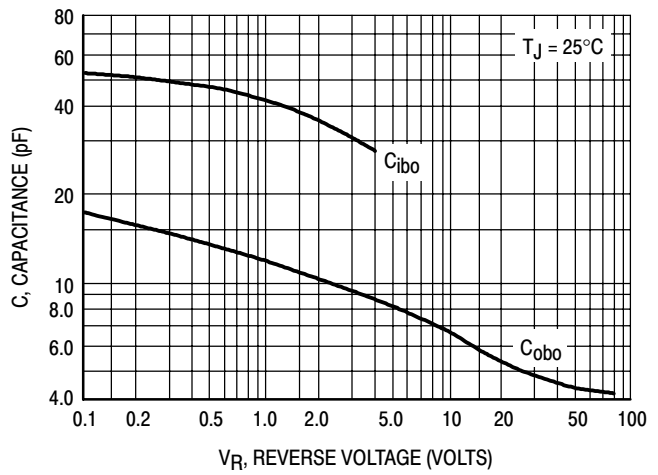


Figure 3. Capacitance

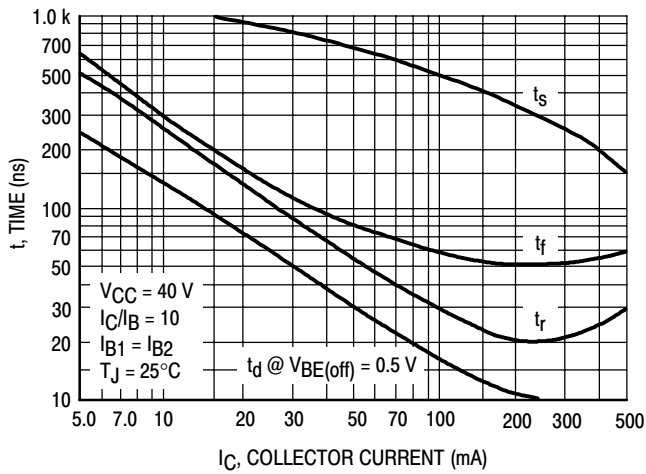


Figure 4. Switching Time

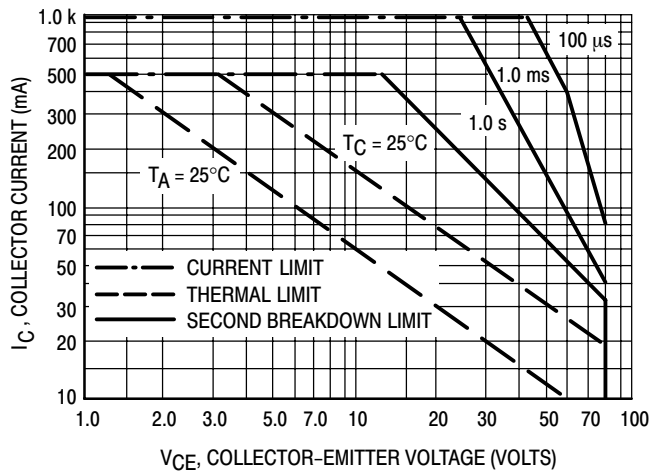


Figure 5. Active-Region Safe Operating Area

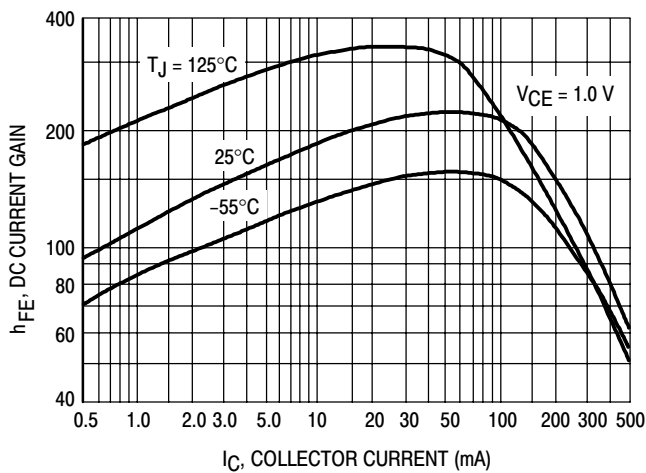


Figure 6. DC Current Gain

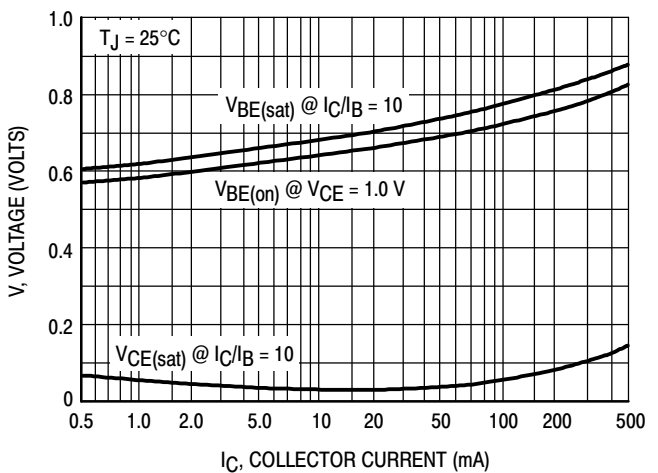


Figure 7. "ON" Voltages

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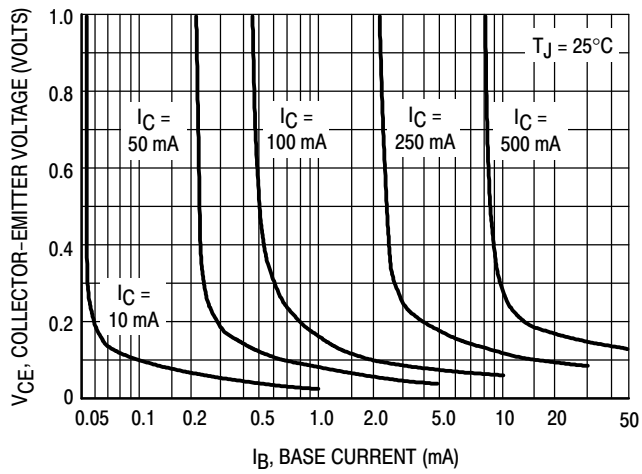


Figure 8. Collector Saturation Region

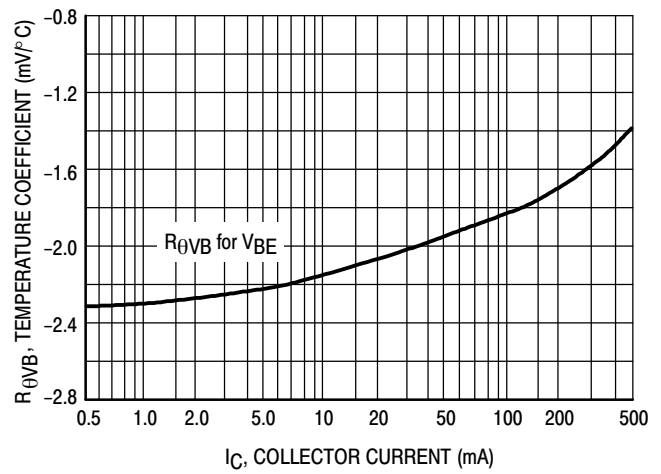


Figure 9. Base-Emitter Temperature Coefficient